


REMARKS

By this Preliminary Amendment claims 3 and 4 have been amended to correct minor typographical errors. Also, claims 1-5 have been amended to correct minor paragraph spacing inconsistencies between the limitations. Finally, Applicant has added new claims 24-28 to recite additional protection to which Applicant is entitled.

Submitted concurrently is a *Petition to Withdraw from Issue Under 37 CFR §1.313* and *Request for Continued Examination (RCE)*. Examination on the merits is requested.

Respectfully submitted,



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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

Please amend claims 1-5 as follows:

1. A method for manufacturing a semiconductor device comprising the steps of:

forming an interlayer insulator comprising at least upper and lower layers, each comprising different dry etching characteristics;

etching the upper layer of the interlayer insulator using a first mask, wherein the lower layer of the interlayer insulator is used as an etching stopper;[]

forming a second mask to cover a portion of the lower layer of the interlayer insulator, which is exposed by the etching step; and

selectively etching the lower layer of the interlayer insulator using the second mask to form a contact hole.

2. A method for manufacturing a semiconductor device comprising at least one thin film transistor comprising the steps of:

forming a first conductive film on a gate insulating film;

patterning the first conductive film to form a gate electrode;

forming an interlayer insulator comprising at least two layers on the gate insulating film;

removing a part of an upper layer of the interlayer insulator, the part being located over at least one of a source region and a drain region;

forming a contact hole through the interlayer insulator to reach at least one of the source region and the drain region;

forming a second conductive film;

patterning the second conductive film to form a pixel electrode;[]

forming a third conductive film; and

patterning the third conductive film to form at least one of a source electrode and a drain electrode, which is in electrical contact with the pixel electrode.

3. (Amended) A method for manufacturing a semiconductor device comprising at least one thin film transistor, comprising the steps of:

forming a first conductive film comprising aluminum on a gate insulating film;

patterning the first conductive film for forming a gate electrode;

forming an interlayer insulator comprising at least two layers on said gate insulating film;

removing a part of an upper layer of the interlayer insulator, the part being located over at least one of a source region and a drain region;

forming a contact hole through [te] the interlayer insulator to reach at least one of the source region and the drain region;

forming a second conductive film;

patterning the second conductive film for forming a pixel electrode;

forming a third conductive film; and

patterning the third conductive film for forming at least one of a source electrode and a drain electrode, which is in electrical contact with said pixel electrode.

4. A method for manufacturing a semiconductor device comprising at least one thin film transistor, comprising the steps of:

forming a first conductive film on a gate insulating film;[]

patterning the first conductive film to form a gate electrode;[]

forming an interlayer insulator comprising at least two layers on said gate insulating film;

removing a part of an upper layer of the interlayer insulator, the part being located over at least one of a source region and a drain region;

forming a contact hole to reach at least one of the source region and the drain region;

forming a second conductive film;
patterning the second conductive film to form a pixel electrode;[]
forming a third conductive film; and
patterning the third conductive film to form at least one of a source electrode and a drain electrode, which is in electrical contact with said pixel electrode, wherein the contact hole is formed smaller than the part.

5. A method for manufacturing a semiconductor device comprising at least one thin film transistor comprising the steps of:
- forming a first conductive film on a gate insulating film;[]
 - patterning the first conductive film to form a gate electrode;[]
 - forming an interlayer insulator on the gate insulating film;
 - removing a part of the interlayer insulator, the part being located over at least one of a source region and a drain region;
 - forming a contact hole through the interlayer insulator to reach at least one of the source region and the drain region;
 - forming a second conductive film;
 - patterning the second conductive film to form a pixel electrode;[]
 - forming a third conductive film; and
 - patterning the third conductive film to form at least one of a source electrode and a drain electrode, which is in electrical contact with the pixel electrode.